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Dual P-Channel 20-V (D-S) MOSFET

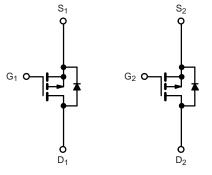
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^{d, e}	Q _g (Typ.)		
- 20	0.048 at V _{GS} = - 4.5 V	- 5	7 nC		
	0.065 at V _{GS} = - 2.5 V	- 3	7 110		

FEATURES

- DT-Trench Power MOSFET
- 100 % UIS Tested

APPLICATIONS

- Load Switches
 - Notebook PCs
 - Desktop PCs
 - Game Stations





P-Channel MOSFET

		SO-8			
S ₁	1			8	D ₁
G_1	2		ı	7	D_1
S_2	3		ļ	6	D_2
G_2	4		Ì	5	D_2
		Top View			

ABSOLUTE MAXIMUM RATINGS T	A = 25 °C, unless other	erwise noted		
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 20	V	
Gate-Source Voltage		V_{GS}	± 12	V
	T _C = 25 °C		- 5.0 ^e	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	1 . [- 4.0 ^e	
Continuous Diain Curient (1) = 130 °C)	T _A = 25 °C	l _D	- 3.3 ^{a, b}	
	T _A = 70 °C		- 2.5 ^{a, b}	Α
Pulsed Drain Current		I _{DM}	- 20 ^e	
Ocationary Oceana Basis Biodo Oceana	T _C = 25 °C	- I _S	- 4	
Continuous Source-Drain Diode Current	T _A = 25 °C	's	- 2.9 ^{a, b}	
Avalanche Current	L = 0.1 mH	I _{AS}	- 10	
Single-Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	15	mJ
	T _C = 25 °C		5.0	
Maximum Power Dissipation	T _C = 70 °C		2.2	w
	T _A = 25 °C	P _D	1.5 ^{a, b}	VV
	T _A = 70 °C	1	0.8 ^{a, b}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c}	t ≤ 10 s	R _{thJA}	30	40	°C/W	
Maximum Junction-to-Foot	Steady State	R_{thJF}	15	20]	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. t = 10 s.
- c. Maximum under Steady State conditions is 85 °C/W.
- d. Based on $T_C = 25$ °C.
- e. Limited by package.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 25		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1D = - 230 μΑ		4.0		miv/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 0.5		- 1.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 15 V, V _{GS} = 0 V			- 1		
		V _{DS} = - 15 V, V _{GS} = 0 V, T _J = 55 °C			- 5	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 20			Α	
	D	V _{GS} = - 4.5 V, I _D = - 4 A		0.048	0.055	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 2.4 A		0.065	0.073		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 4 A		23		S	
Dynamic ^b				•			
Input Capacitance	C _{iss}			1296			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		205		pF	
Reverse Transfer Capacitance	C _{rss}			118			
Total Gate Charge		$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4 \text{ A}$	- 4 A	7		nC	
Total Gate Charge	Q_g			5.5			
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -2.5 \text{ V}, I_{D} = -2.4 \text{ A}$		2			
Gate-Drain Charge	Q _{gd}			1.5			
Gate Resistance	R_g	f = 1 MHz		6.8		Ω	
Turn-On Delay Time	t _{d(on)}			7			
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 15 \Omega$		6.3]	
Turn-Off DelayTime	ne $t_{d(off)}$ $I_{D} \cong -1$			45			
Fall Time	t _f	Ω		10		ns	
Turn-On Delay Time	t _{d(on)}			6			
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$		3.5			
Turn-Off DelayTime	t _{d(off)}	$I_D \cong -1 \text{ A, V}_{GEN} = -2.5 \text{ V, R}_g = 1 \Omega$		40			
Fall Time	t _f			6			
Drain-Source Body Diode Characterist	ics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4	Α	
Pulse Diode Forward Current	I _{SM}				- 20	7 ^	
Body Diode Voltage	V _{SD}	I _S = -2 A, V _{GS} = 0 V		- 0.7	- 1.0	V	
Body Diode Reverse Recovery Time t		I = 2 A dl/dt = 100 A/va T = 05 °C		14		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = -2 \text{ A, dI/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 \text{ °C}$		3.5		nC	

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

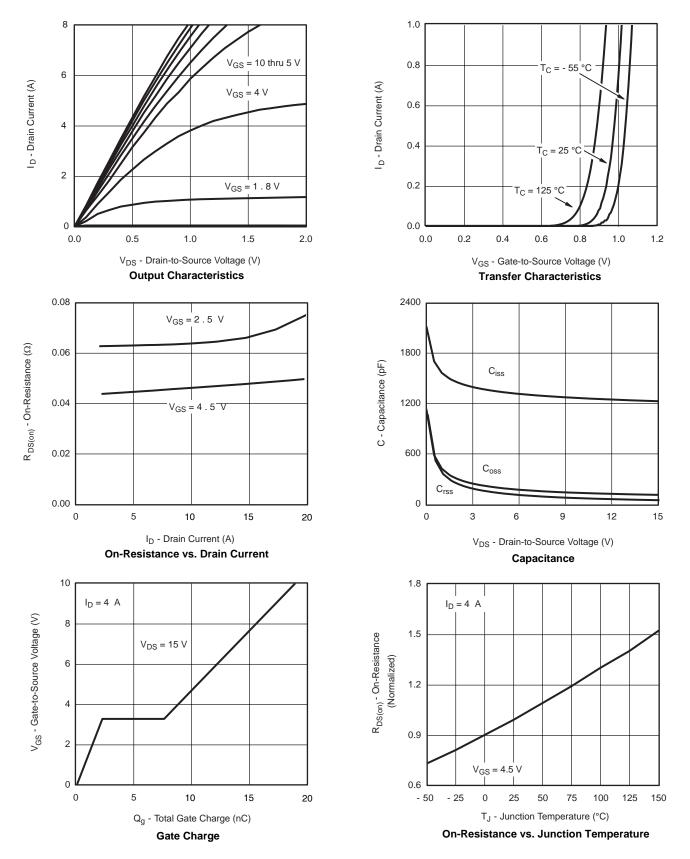
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.





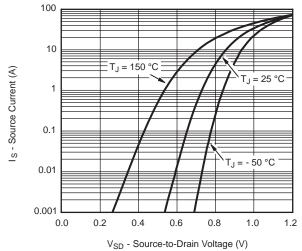
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



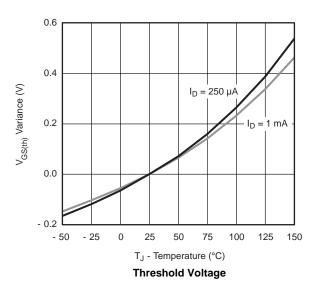




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

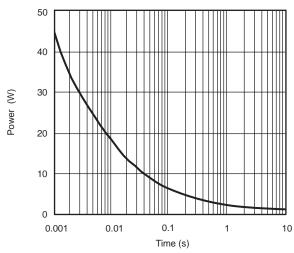


Source-Drain Diode Forward Voltage

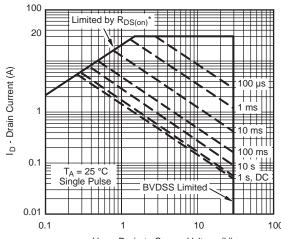


0.20 $I_D = 3 A$ 0.16 $R_{DS(on)}$ - On-Resistance (Ω) 0.12 T_J = 125 °C 0.08 0.04 T_J = 25 °C 0.00 6 0 8 10

V_{GS} - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



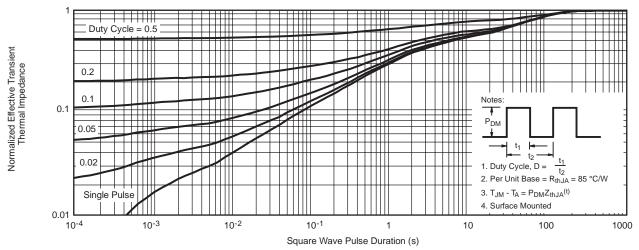
V_{DS} - Drain-to-Source Voltage (V)

* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

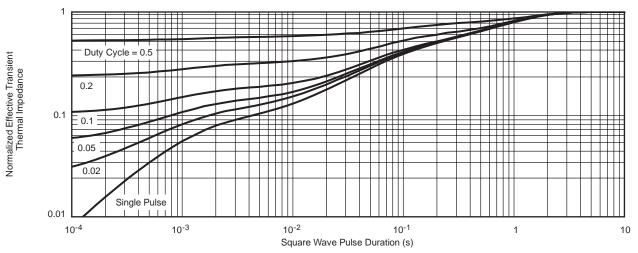
Safe Operating Area



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot





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